

STD5406NT4G-VB Datasheet N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^{a, c}	Q _g (Typ.)		
40	0.0050 at V _{GS} = 10 V	85	80 nC		
40	0.0065 at V _{GS} = 4.5 V	70	OU IIC		

TO-252

FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested



Unit ٧

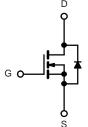
Α

Unit

°C/W

APPLICATIONS

- Synchronous Rectification
- Power Supplies



SFET

250

80

Typical

32

0.33

Maximum

40

0.4

G D S			0 S
			N-Channel MOS
ABSOLUTE MAXIMUM RATINGS T	_A = 25 °C, unle	ss otherwise n	oted
Parameter		Symbol	Limit
Drain-Source Voltage		V _{DS}	40
Gate-Source Voltage		V _{GS}	± 25
	T _C = 25 °C		85 ^{a, c}
Continuous Drain Current (T _J = 175 °C)	T _C = 70 °C	ı	70 ^c
Continuous Diam Current (1 j = 173 C)	T _A = 25 °C	I _D	59 ^b
	T _A = 70 °C		53 ^b

Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	320	mJ
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S 110 ^{a, c} 2.6 ^b 312 ^a 200	110 ^{a, c}	А
Continuous Source-Diain Diode Current	T _A = 25 °C		2.6 ^b	^
	T _C = 25 °C	- P _D	312 ^a	
Maximum Power Dissipation	T _C = 70 °C		200	\Box w
Maximum Fower Dissipation	T _A = 25 °C		3.13 ^b	v
	T _A = 70 °C		2.0 ^b	
Operating Junction and Storage Temperature R	ange	T _J , T _{stg}	- 55 to 150	°C

L = 0.1 mH

Steady State

Steady State

 I_{DM}

 I_{AS}

Symbol

 R_{thJA}

 $\mathsf{R}_{\mathsf{thJC}}$

Parameter

a. Based on $T_C = 25$ °C.

Pulsed Drain Current

Avalanche Current Pulse

b. Surface Mounted on 1" x 1" FR4 board.

Maximum Junction-to-Ambient^b

Maximum Junction-to-Case

c. Calculated based on maximum junction temperature. Package limitation current is 110 A.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		41		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	10 = 200 μΛ		- 8		IIIV/ C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.2		2.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Coto Voltago Drain Current	l	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α	
David Common Con Otata Basista and	D	V _{GS} = 10 V, I _D = 30 A		0.0050			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0065		Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		180		S	
Dynamic ^b							
Input Capacitance	C _{iss}			2380		pF	
Output Capacitance	C _{oss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		550			
Reverse Transfer Capacitance	C _{rss}			250			
Total Gate Charge	Q_g			80	120	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		20			
Gate-Drain Charge	Q _{gd}			12			
Gate Resistance	R _g	f = 1 MHz		0.85	1.3	Ω	
Turn-On Delay Time	t _{d(on)}			20	30		
Rise Time	t _r	V_{DD} = 20 V, R_L = 1.0 Ω		11	17		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 20$ A, V_{GEN} = 10 V, R_g = 1 Ω		77	115		
Fall Time	t _f			10	15		
Turn-On Delay Time	t _{d(on)}			102	155	ns	
Rise Time	t _r	V_{DD} = 20 V, R_L = 1.0 Ω		62	95		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 20 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		180	270		
Fall Time	t _f			60	90		
Drain-Source Body Diode Characteristic	s					1	
Continuous Source-Drain Diode Current	Is	T _C = 25 °C			110		
Pulse Diode Forward Current ^a	I _{SM}				200	А	
Body Diode Voltage	V _{SD}	I _S = 20 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			50	75	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _J = 25 °C		70	105	nC	
Reverse Recovery Fall Time	t _a			30			
Reverse Recovery Rise Time	<u> </u>			20		ns	

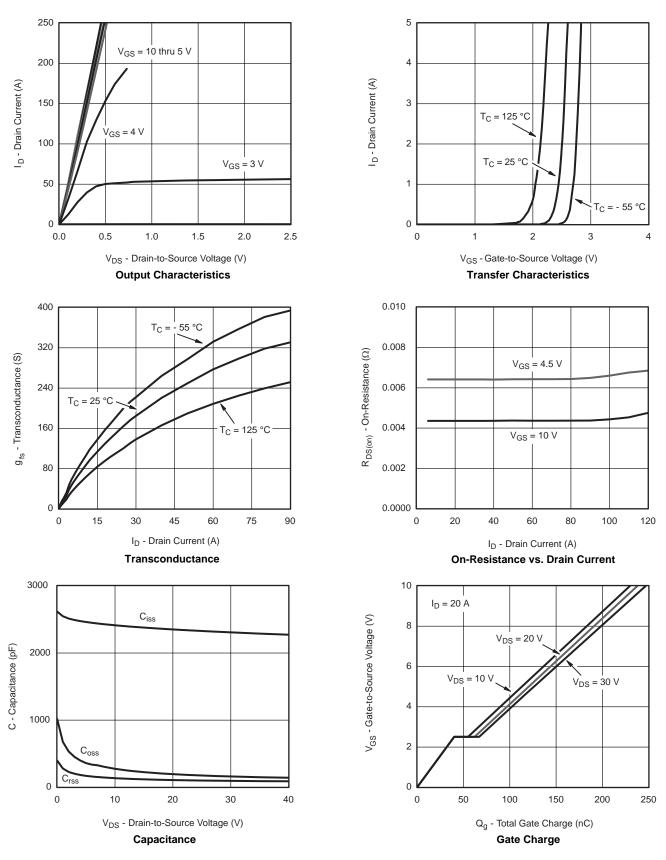
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

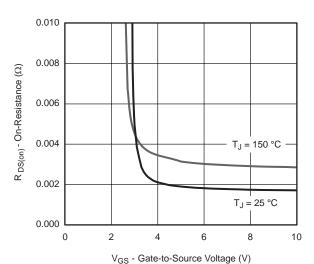




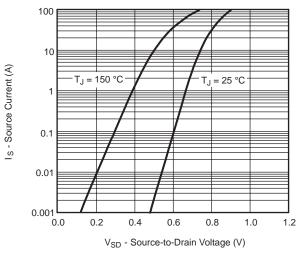
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Forward Diode Voltage vs. Temperature



Threshold Voltage

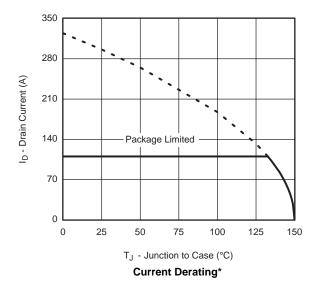


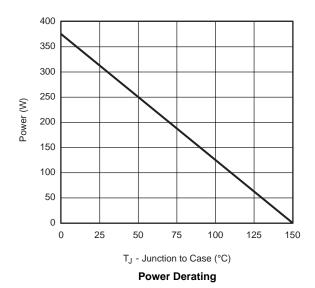
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





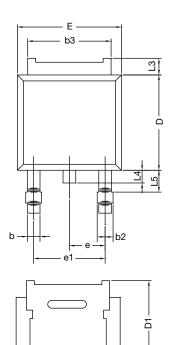
* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

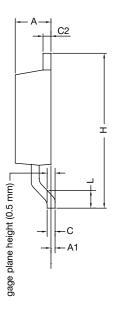


Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE





	MILLIMETERS		INC	INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC		0.090 BSC		
e1	4.56 BSC		0.180 BSC		
Ш	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12					

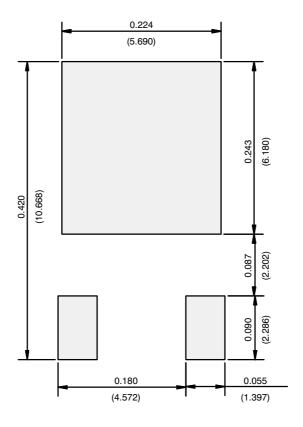
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)



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